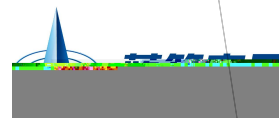


SOP-8                      N

N-Channel Enhancement Mode Field Effect Transistor in a SOP-

Parameter

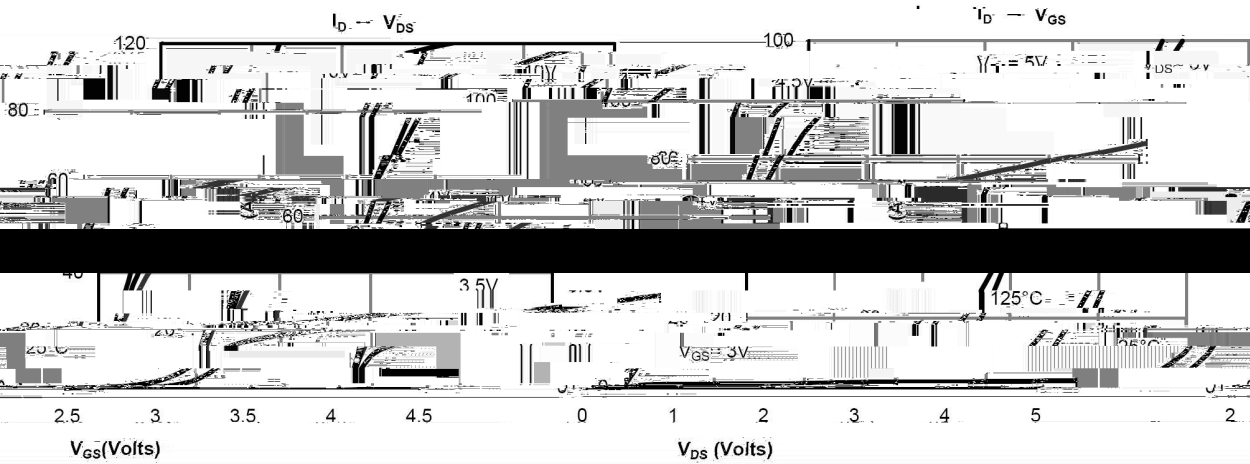
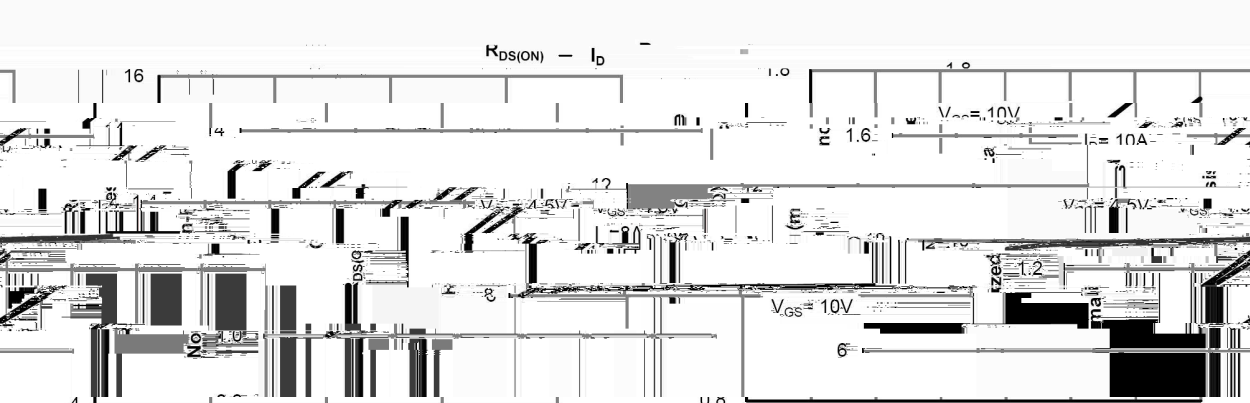
Symbp



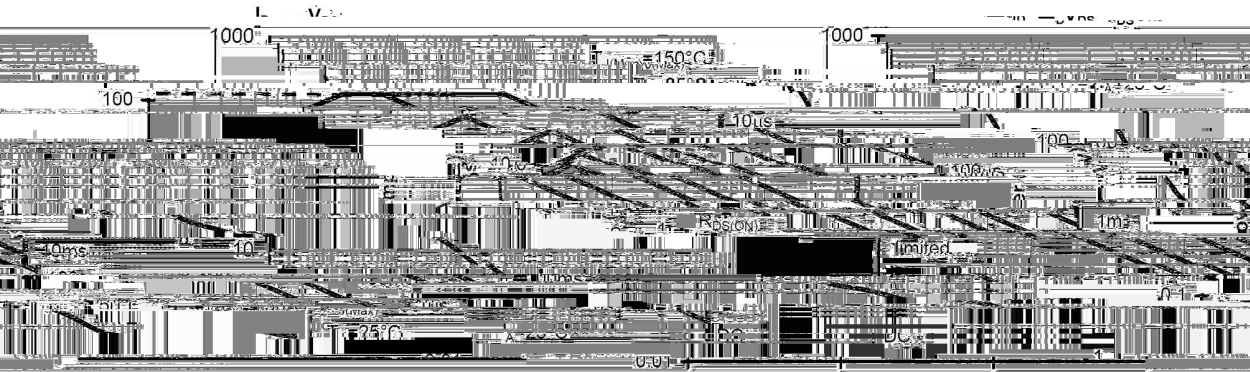
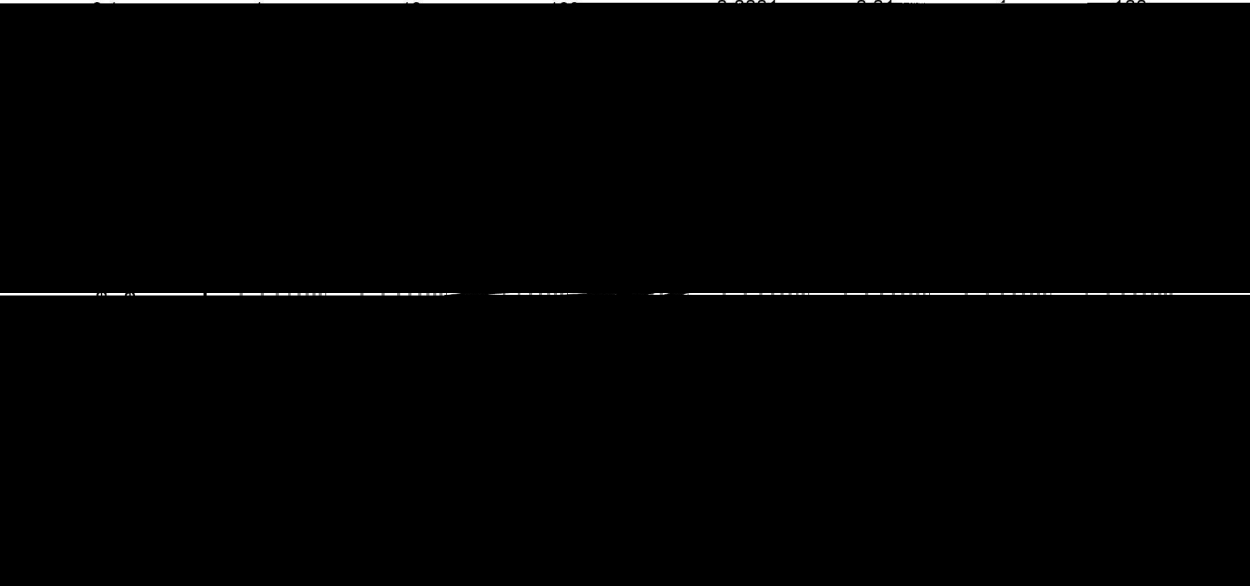
## / Electrical Characteristics(Ta=25 )

| Parameter                    | V<br>Symbol | Test Conditions                        |  | Typ  | Max  | Unit |
|------------------------------|-------------|----------------------------------------|--|------|------|------|
| Input Capacitance            | $C_{iss}$   | $V_{DS}=15V$ $V_{GS}=0V$<br>$f=1.0MHz$ |  | 1500 | 1950 | pF   |
| Output Capacitance           | $C_{oss}$   |                                        |  | 215  |      |      |
| Reverse Transfer Capacitance | $C_{rss}$   |                                        |  | 135  |      |      |
| Total Gate Charge(10V)       | $Q_g$       | $V_{DS}=20V$ $I_D=10A$<br>$V_{GS}=10V$ |  |      |      |      |

/ Electrical Characteristic Curve



/ Electrical Characteristic Curve



/ Package Dimensions





## ( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

- |   |         |           |                                         |
|---|---------|-----------|-----------------------------------------|
| 1 | 150 180 | 60 90sec; | 1.Preheating:150~180 , Time:60~90sec.   |
| 2 | 245±5   | 5±0.5sec; | 2.Peak Temp.:245±5 , Duration:5±0.5sec. |
| 3 |         |           |                                         |